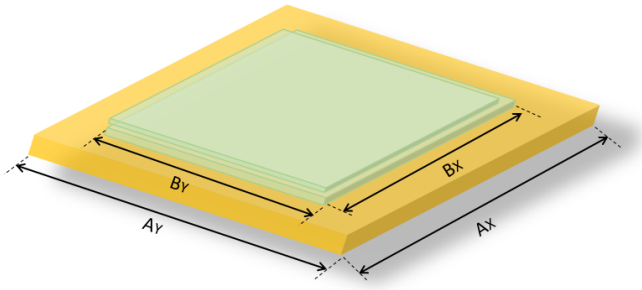
FB-5VS32

Chip Bi-directional TVS diode



Mechanical Data	Notes
Dice size	AX=AY=380um/BX=BY=180um
Wafer size	4” (Gross die:45,620pcs/Good die>42,427pcs)
Chip Thickness	230um±20um
Scribe line width	60um
Top metal	Al/Au/Ag
Back side metal	Al/Au/Ag/Sn

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	VRWM		5	V
Peak pulse power	PPP	Tp=8/20us	140*	W
Peak pulse current	IPP	Tp=8/20us	10*	A
Electrostatic discharge	VESD	IEC61000-4-2 Level 4	± 8(Contact) ±15(Air)	KV
Max.junction temp.	Tj		150	℃

Characteristics TA=25℃

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	VBR	IT=1mA	5.6		9.4	V
Reverse leakage current	IR	V=± 5V			0.09	uA
Clamping Voltage	VC	IPP=1.0A IPP=10A			12.0* 14.0*	V
Diode capacitance	Cj	VR=0V f=1MHz		15.0	20.0	pf

Notes:

(1)sampling testing:no bad dice inking/guaranteed good die >93%

(2)Testing follow customer

(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation, Pr-revers power dissipation

(4)**For device testing